

NTB6413AN, NTP6413AN, NVB6413AN



ON Semiconductor®

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N-Channel Power MOSFET 100 V, 42 A, 28 mΩ

Features

- Low $R_{DS(on)}$
- High Current Capability
- 100% Avalanche Tested
- NVB Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ Unless otherwise specified)

Parameter		Symbol	Value	Unit	
Drain-to-Source Voltage		V_{DSS}	100	V	
Gate-to-Source Voltage – Continuous		V_{GS}	± 20	V	
Continuous Drain Current $R_{\theta JC}$	Steady State	I_D	$T_C = 25^\circ\text{C}$	42	A
			$T_C = 100^\circ\text{C}$	28	
Power Dissipation $R_{\theta JC}$	Steady State	P_D	$T_C = 25^\circ\text{C}$	136	W
Pulsed Drain Current	$t_p = 10 \mu\text{s}$	I_{DM}	178	A	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 to +175	$^\circ\text{C}$	
Source Current (Body Diode)		I_S	42	A	
Single Pulse Drain-to-Source Avalanche Energy ($V_{DD} = 50 \text{ Vdc}$, $V_{GS} = 10 \text{ Vdc}$, $I_{L(pk)} = 36.5 \text{ A}$, $L = 0.3 \text{ mH}$, $R_G = 25 \Omega$)		E_{AS}	200	mJ	
Lead Temperature for Soldering Purposes, 1/8" from Case for 10 Seconds		T_L	260	$^\circ\text{C}$	

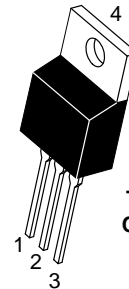
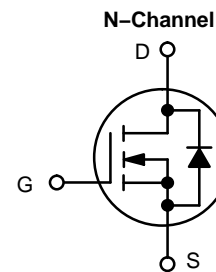
THERMAL RESISTANCE RATINGS

Parameter	Symbol	Max	Unit
Junction-to-Case (Drain) Steady State	$R_{\theta JC}$	1.1	$^\circ\text{C/W}$
Junction-to-Ambient (Note 1)	$R_{\theta JA}$	35	

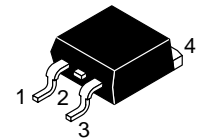
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Surface mounted on FR4 board using 1 sq in pad size, (Cu Area 1.127 sq in [2 oz] including traces).

$V_{(BR)DSS}$	$R_{DS(ON) MAX}$	$I_D MAX$ (Note 1)
100 V	28 mΩ @ 10 V	42 A

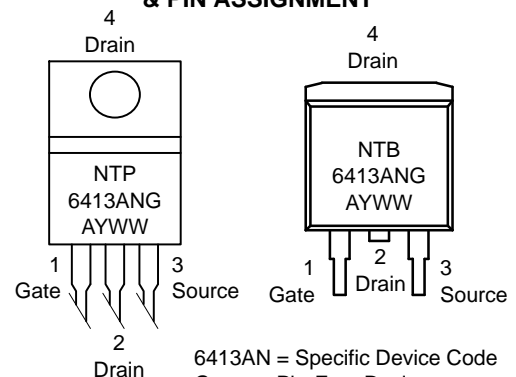


TO-220AB
CASE 221A
STYLE 5



D²PAK
CASE 418B
STYLE 2

MARKING DIAGRAM & PIN ASSIGNMENT



6413AN = Specific Device Code
G = Pb-Free Device
A = Assembly Location
Y = Year
WW = Work Week

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

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ELECTRICAL CHARACTERISTICS (T_J = 25°C Unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0 V, I _D = 250 μA	100			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	V _{(BR)DSS} /T _J			115		mV/°C
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V, V _{DS} = 100 V	T _J = 25°C		1.0	μA
			T _J = 125°C		100	
Gate-to-Source Leakage Current	I _{GSS}	V _{DS} = 0 V, V _{GS} = ±20 V			±100	nA

ON CHARACTERISTICS (Note 2)

Gate Threshold Voltage	V _{GS(th)}	V _{GS} = V _{DS} , I _D = 250 μA	2.0		4.0	V
Negative Threshold Temperature Coefficient	V _{GS(th)} /T _J			8.1		mV/°C
Drain-to-Source On-Resistance	R _{DS(on)}	V _{GS} = 10 V, I _D = 42 A		25.6	28	mΩ
Forward Transconductance	g _{FS}	V _{GS} = 5 V, I _D = 20 A		17.9		S

CHARGES, CAPACITANCES & GATE RESISTANCE

Input Capacitance	C _{iss}	V _{DS} = 25 V, V _{GS} = 0 V, f = 1 MHz		1800		pF
Output Capacitance	C _{oss}			280		
Reverse Transfer Capacitance	C _{rss}			100		
Total Gate Charge	Q _{G(TOT)}	V _{GS} = 10 V, V _{DS} = 80 V, I _D = 42 A		51		nC
Threshold Gate Charge	Q _{G(TH)}			2.0		
Gate-to-Source Charge	Q _{GS}			10		
Gate-to-Drain Charge	Q _{GD}			26		
Plateau Voltage	V _{GP}				5.8	
Gate Resistance	R _G			2.4		Ω

SWITCHING CHARACTERISTICS, V_{GS} = 10 V (Note 3)

Turn-On Delay Time	t _{d(on)}	V _{GS} = 10 V, V _{DD} = 80 V, I _D = 42 A, R _G = 6.2 Ω		13		ns
Rise Time	t _r			84		
Turn-Off Delay Time	t _{d(off)}			52		
Fall Time	t _f			71		

DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V _{SD}	I _S = 42 A	T _J = 25°C		0.92	1.3	V
			T _J = 125°C		0.83		
Reverse Recovery Time	t _{rr}	V _{GS} = 0 V, I _S = 42 A, dI _{SD} /dt = 100 A/μs		73		ns	
Charge Time	t _a			56			
Discharge Time	t _b			17			
Reverse Recovery Charge	Q _{RR}				230		

2. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.
3. Switching characteristics are independent of operating junction temperatures.

TYPICAL CHARACTERISTICS

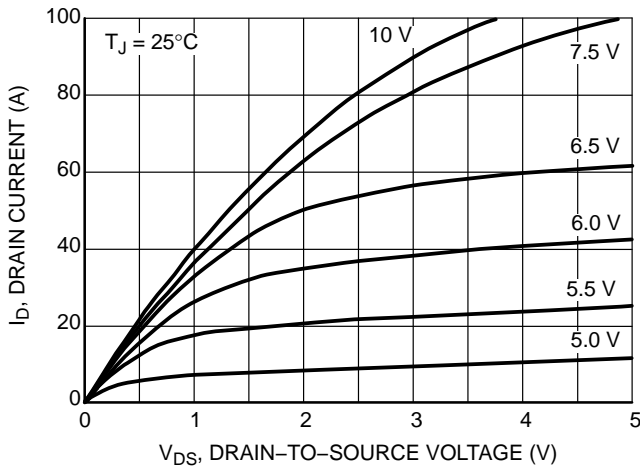


Figure 1. On-Region Characteristics

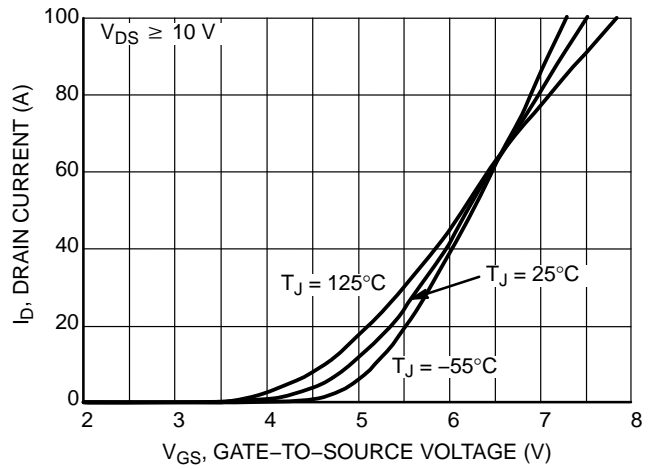


Figure 2. Transfer Characteristics

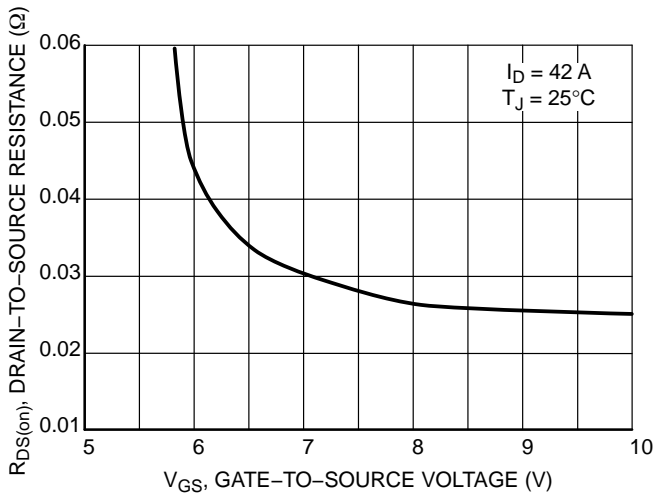


Figure 3. On-Region versus Gate Voltage

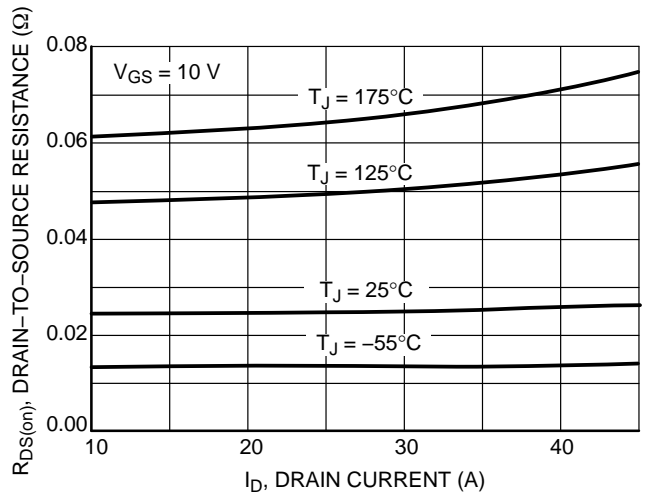


Figure 4. On-Resistance versus Drain Current and Gate Voltage

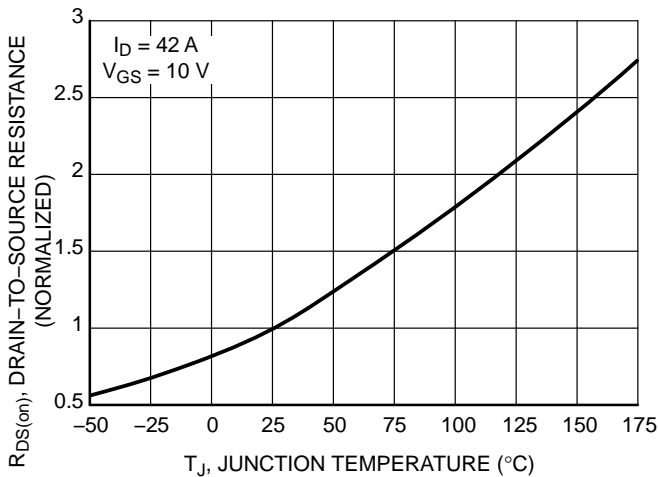


Figure 5. On-Resistance Variation with Temperature

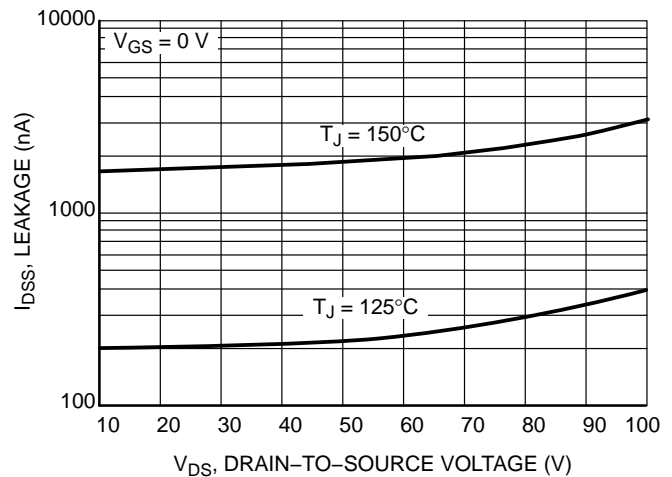


Figure 6. Drain-to-Source Leakage Current versus Voltage

TYPICAL CHARACTERISTICS

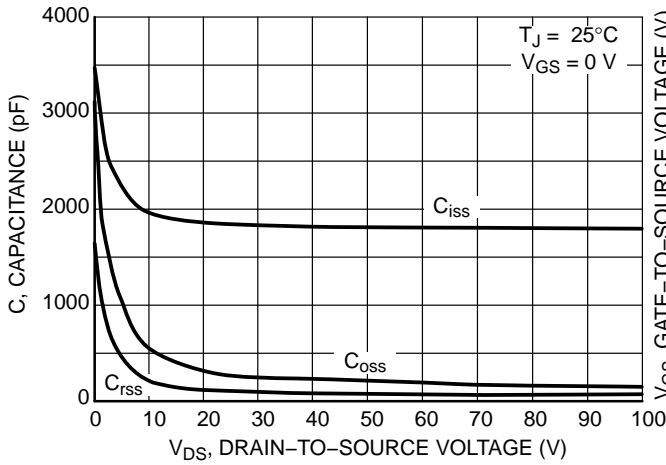


Figure 7. Capacitance Variation

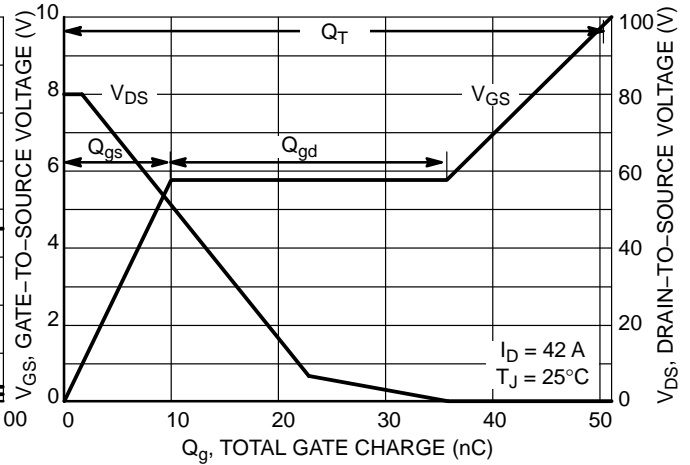


Figure 8. Gate-to-Source Voltage and Drain-to-Source Voltage versus Total Charge

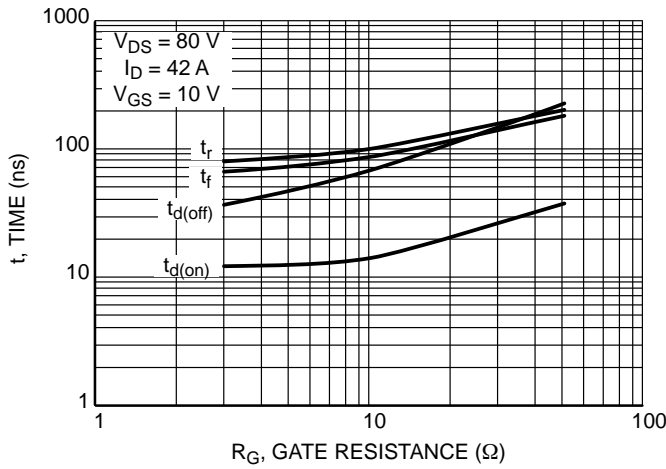


Figure 9. Resistive Switching Time Variation versus Gate Resistance

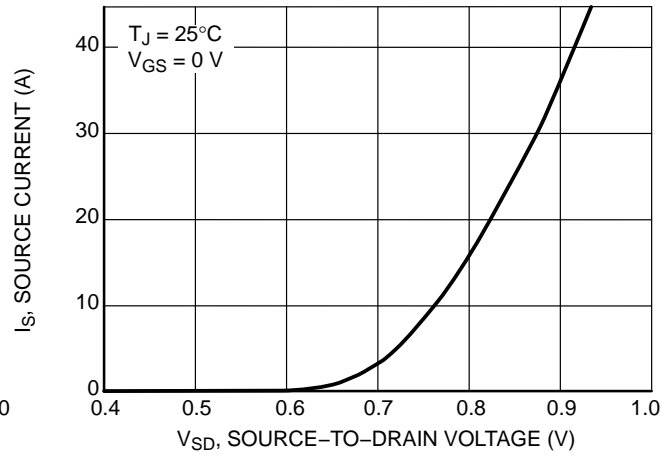


Figure 10. Diode Forward Voltage versus Current

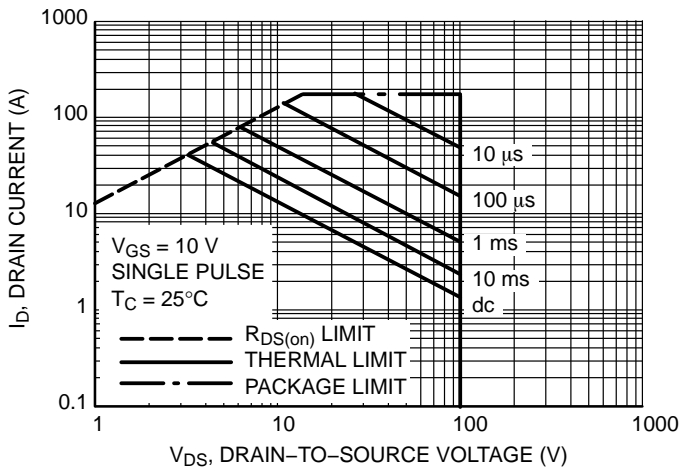


Figure 11. Maximum Rated Forward Biased Safe Operating Area

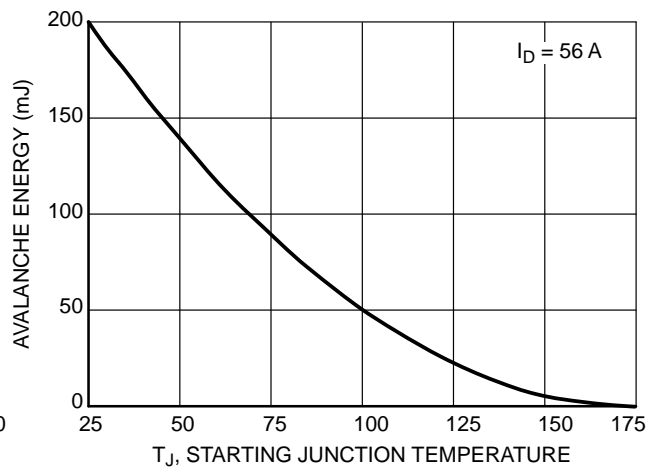


Figure 12. Maximum Avalanche Energy versus Starting Junction Temperature

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TYPICAL CHARACTERISTICS

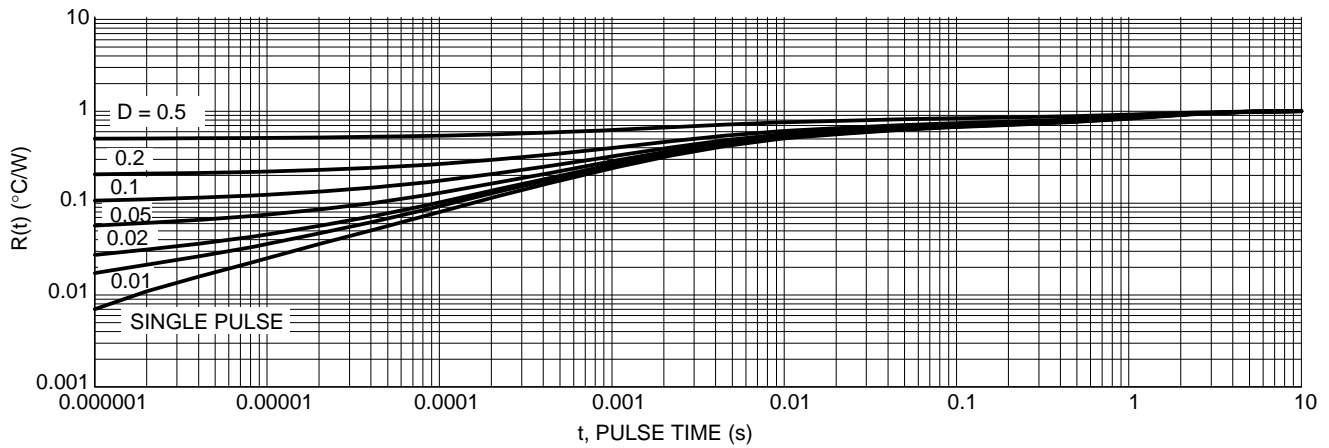


Figure 13. Thermal Response

ORDERING INFORMATION

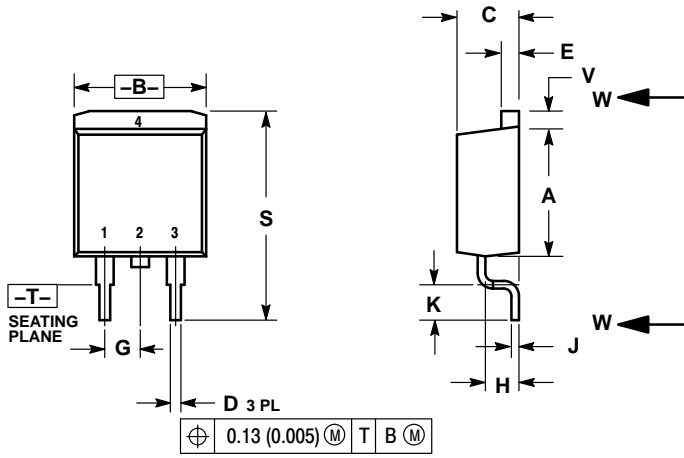
Device	Package	Shipping†
NTB6413ANG	D ² PAK (Pb-Free)	50 Units / Rail
NTB6413ANT4G	D ² PAK (Pb-Free)	800 / Tape & Reel
NTP6413ANG	TO-220 (Pb-Free)	50 Units / Rail
NVB6413ANT4G	D ² PAK (Pb-Free)	800 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

NTB6413AN, NTP6413AN, NVB6413AN

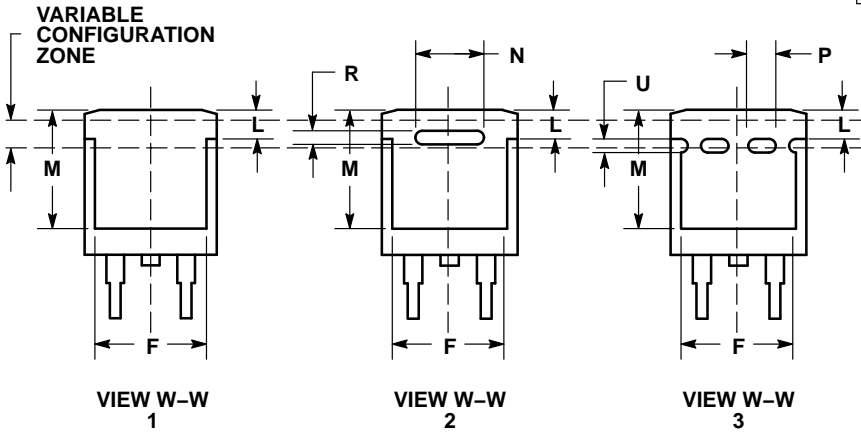
PACKAGE DIMENSIONS

D²PAK 3 CASE 418B-04 ISSUE K



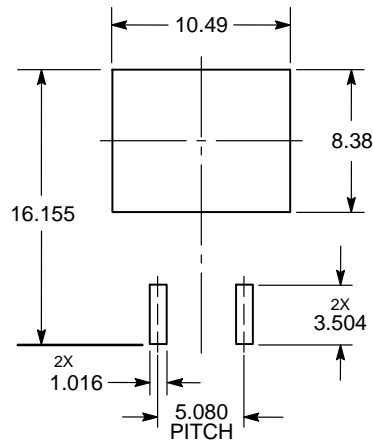
- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. 418B-01 THRU 418B-03 OBSOLETE, NEW STANDARD 418B-04.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.340	0.380	8.64	9.65
B	0.380	0.405	9.65	10.29
C	0.160	0.190	4.06	4.83
D	0.020	0.035	0.51	0.89
E	0.045	0.055	1.14	1.40
F	0.310	0.350	7.87	8.89
G	0.100 BSC		2.54 BSC	
H	0.080	0.110	2.03	2.79
J	0.018	0.025	0.46	0.64
K	0.090	0.110	2.29	2.79
L	0.052	0.072	1.32	1.83
M	0.280	0.320	7.11	8.13
N	0.197 REF		5.00 REF	
P	0.079 REF		2.00 REF	
R	0.039 REF		0.99 REF	
S	0.575	0.625	14.60	15.88
V	0.045	0.055	1.14	1.40



- STYLE 2:
PIN 1. GATE
2. DRAIN
3. SOURCE
4. DRAIN

SOLDERING FOOTPRINT*



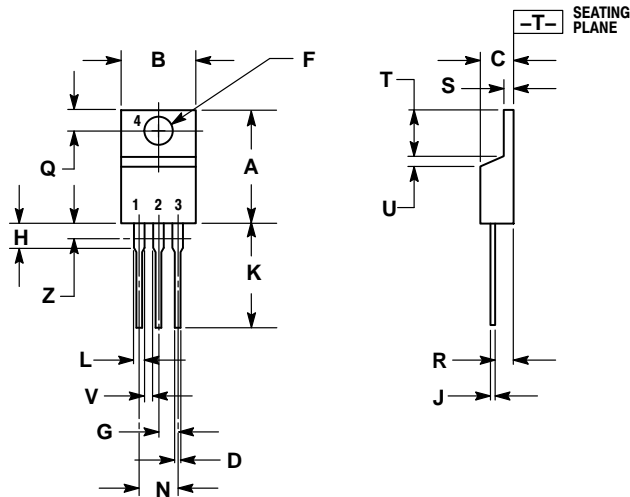
DIMENSIONS: MILLIMETERS

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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PACKAGE DIMENSIONS

TO-220
CASE 221A-09
ISSUE AH



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.570	0.620	14.48	15.75
B	0.380	0.415	9.66	10.53
C	0.160	0.190	4.07	4.83
D	0.025	0.038	0.64	0.96
F	0.142	0.161	3.61	4.09
G	0.095	0.105	2.42	2.66
H	0.110	0.161	2.80	4.10
J	0.014	0.024	0.36	0.61
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045	---	1.15	---
Z	---	0.080	---	2.04

STYLE 5:

1. GATE
2. DRAIN
3. SOURCE
4. DRAIN

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